# **Quad 2-Input NAND Gate with Open-Drain Outputs**

# **High-Performance Silicon-Gate CMOS**

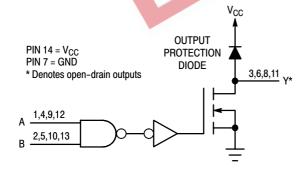
The MC74HC03A is identical in pinout to the LS03. The device inputs are compatible with Standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC03A NAND gate has, as its outputs, a high-performance MOS N-Channel transistor. This NAND gate can, therefore, with a suitable pullup resistor, be used in wired-AND applications. Having the output characteristic curves given in this data sheet, this device can be used as an LED driver or in any other application that only requires a sinking current.

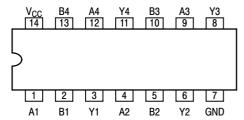
## **Features**

- Output Drive Capability: 10 LSTTL Loads With Suitable Pullup Resistor
- Outputs Directly Interface to CMOS, NMOS and TTL
- High Noise Immunity Characteristic of CMOS Devices
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1µA
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 28 FETs or 7 Equivalent Gates
- Pb-Free Packages are Available

# LOGIC DIAGRAM



Pinout: 14-Lead Packages (Top View)

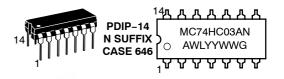




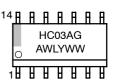
# ON Semiconductor®

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# MARKING DIAGRAMS









TSSOP-14 DT SUFFIX CASE 948G



A = Assembly Location

WL or L = Wafer Lot YY or Y = Year

WW or W = Work Week

G or ■ = Pb–Free Package (Note: Microdot may be in either location)

**FUNCTION TABLE** 

Inputs		Output
Α	В	Υ
L	L	Z
L	Н	Z
Н	L	Z
Н	Н	L

Z = High Impedance

## **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	$-0.5$ to $V_{CC}$ + $0.5$	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	$-0.5$ to $V_{CC}$ + $0.5$	V
l <sub>in</sub>	DC Input Current, per Pin	±[ <b>2</b> 0	mA
l <sub>out</sub>	DC Output Current, per Pin	±[ <b>2</b> 5	mA
Icc	DC Supply Current, V <sub>CC</sub> and GND Pins	±[ <b>5</b> 0	mA
P <sub>D</sub>	Power Dissipation in Still Air Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ . Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

# RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	Vcc	٧
T <sub>A</sub>	Operating Temperature, All Package Types	<b>–</b> 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time $V_{CC} = 2.0 \text{ V}$ (Figure 1) $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0	1000	ns
	(Figure 1) V <sub>CC</sub> = 4.5 V	0	500	
	$V_{CC} = 6.0 \text{ V}$	0	400	

#### **DESIGN GUIDE**

Criteria	Value	Unit
Internal Gate Count*	7.0	ea
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	0.0075	рJ

<sup>\*</sup>Equivalent to a two-input NAND gate

# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74HC03AN	PDIP-14	
MC74HC03ANG	PDIP-14 (Pb-Free)	25 Units/Rail
MC74HC03AD	SOIC-14	
MC74HC03ADG	SOIC-14 (Pb-Free)	55 Units/Rail
MC74HC03ADR2	SOIC-14	
MC74HC03ADR2G	SOIC-14 (Pb-Free)	2500/Tape & Reel
MC74HC03ADTR2	TSSOP-14*	
MC74HC03ADTR2G	TSSOP-14*	
MC74HC03AFEL	SOEIAJ-14	
MC74HC03AFELG	SOEIAJ-14 (Pb-Free)	2000/Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>This package is inherently Pb-Free.



# DC CHARACTERISTICS (Voltages Referenced to GND)

			v <sub>cc</sub>	Guara	nteed Lin	nit	
Symbol	Parameter	Condition	v	-55 to 25°C	≤85°C	≤125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out} = 0.1V \text{ or } V_{CC} - 0.1V$ $ I_{out}  \le 20 \mu A$	2.0 3.0 4.5 6.0	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	>
V <sub>IL</sub>	Maximum Low-Level Input Voltage	$V_{out} = 0.1V \text{ or } V_{CC} - 0.1V$ $ I_{out}  \le 20\mu\text{A}$	2.0 3.0 4.5 6.0	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	<
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{out} = 0.1V \text{ or } V_{CC} - 0.1V$ $ I_{out}  \le 20 \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	<b>&gt;</b>
		$\begin{aligned} V_{in} = V_{IH} \text{ or } V_{IL} & &  I_{out}  \leq 2.4 \text{mA} \\ &  I_{out}  \leq 4.0 \text{mA} \\ &  I_{out}  \leq 5.2 \text{mA} \end{aligned}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
l <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	±0.1	±1.0	±1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0\mu A$	6.0	1.0	10	40	μΑ
I <sub>OZ</sub>	Maximum Three-State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL}$ or $V_{IH}$ $V_{out} = V_{CC}$ or GND	6.0	±0.5	±5.0	±10	μΑ

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

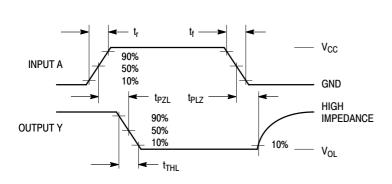
# AC CHARACTERISTICS ( $C_L = 50pF$ , Input $t_r = t_f = 6ns$ )

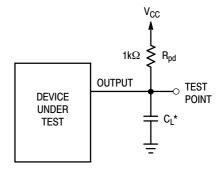
		v <sub>cc</sub>	Guaranteed Limit			
Symbol	Parameter	V	-55 to 25°C	≤85°C	≤125°C	Unit
t <sub>PLZ</sub> ,	Maximum Propagation Delay, Input A or B to Output Y	2.0	120	150	180	ns
$t_{PZL}$	(Figures 1 and 2)	3.0	45	60	75	
		4.5	24	30	36	
		6.0	20	26	31	
t <sub>TLH</sub> ,	Maximum Output Transition Time, Any Output	2.0	75	95	110	ns
t <sub>THL</sub>	(Figures 1 and 2)	3.0	27	32	36	
		4.5	15	19	22	
		6.0	13	16	19	
C <sub>in</sub>	Maximum Input Capacitance		10	10	10	pF
C <sub>out</sub>	Maximum Three-State Output Capacitance (Output in High-Impedance State)		10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V, V <sub>EE</sub> = 0 V		
$C_{PD}$	Power Dissipation Capacitance (Per Buffer)*	8.0	pF	

<sup>\*</sup> Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} \, V_{CC}^{2f} + I_{CC} \, V_{CC}$ . For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

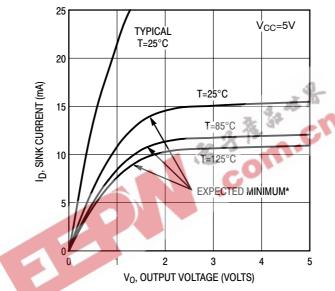




\*Includes all probe and jig capacitance

Figure 1. Switching Waveforms

Figure 2. Test Circuit



\*The expected minimum curves are not guarantees, but are design aids.

Figure 3. Open-Drain Output Characteristics

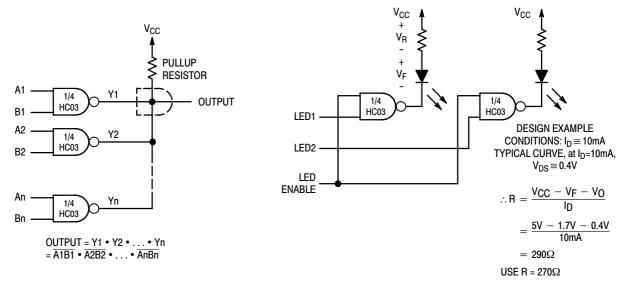
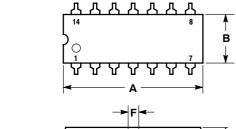


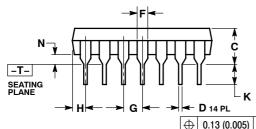
Figure 4. Wired AND

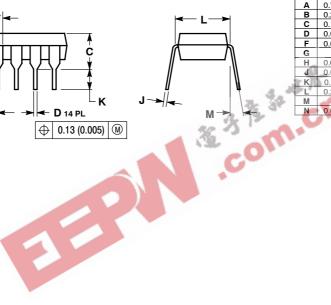
Figure 5. LED Driver With Blanking

# **PACKAGE DIMENSIONS**

PDIP-14 CASE 646-06 ISSUE P





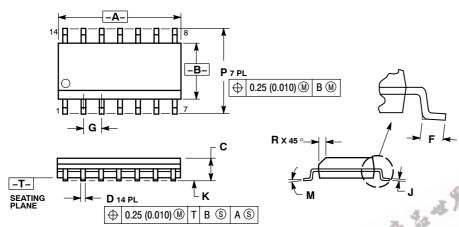


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
  4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
  5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	19.56
В	0.240	0.260	6.10	6.60
С	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100	BSC	2.54	BSC
H	0.052	0.095	1.32	2.41
d	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
T.	0.290	0.310	7.37	7.87
M		10 °		10 °
N	0.015	0.039	0.38	1.01

## **PACKAGE DIMENSIONS**

SOIC-14 CASE 751A-03 **ISSUE H** 

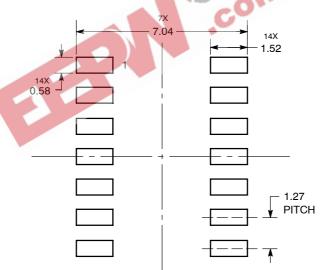


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER

- I. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
   CONTROLLING DIMENSION: MILLIMETER.
   DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
   MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
   DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	ILLIMETERS INCHES		HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
ם	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
_K	0.10	0.25	0.004	0.009
M	0 °	7°	0 °	7°
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

# SOLDERING FOOTPRINT

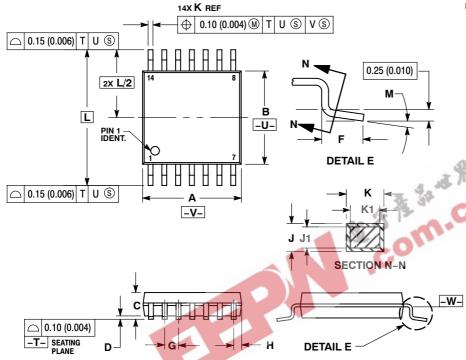


DIMENSIONS: MILLIMETERS

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## PACKAGE DIMENSIONS

TSSOP-14 CASE 948G-01 **ISSUE B** 



- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEPD 0.25 (0.010) PER SIDE.
  - NOT EXCEED 0.25 (0.010) PER SIDE.

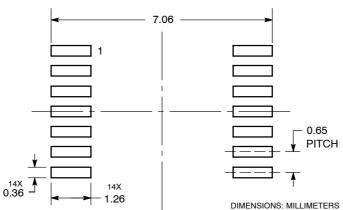
    5. DIMENSION K DOES NOT INCLUDE
    DAMBAR PROTRUSION. ALLOWABLE
    DAMBAR PROTRUSION SHALL BE 0.08
    (0.003) TOTAL IN EXCESS OF THE K (0.003) TOTAL IN EXCESS OF THE K
    DIMENSION AT MAXIMUM MATERIAL
    CONDITION.

    5. TERMINAL NUMBERS ARE SHOWN FOR
    REFERENCE ONLY.

    7. DIMENSION A AND B ARE TO BE
    DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40		0.252 BSC	
M	0°	8 °	0 °	8 °

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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